

November 15

8:00	Registration		
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9:20			
9:30	Opening Remark (Kokura)		
9:40	Best/Young Award Ceremony (Izawa)		
9:50	HERBERT HAROLD SAWIN (Massachusetts Institute of Technology)	Nishizawa Award Lecture	
10:00			
10:10			
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10:40	Richard A. Gottscho (Lam Research Corporation)		
10:50	Break		
11:00	Break		
11:10	A-1 M. Brihoum (LTM-CNRS)	Surface Reaction	
11:20	Roughness formation mechanisms involved in HBr cure		
11:30	A-2 BT. Chan (IMEC)		
11:40	High selective plasma etching for PMMA of block-copolymer in Directed-Self Assembly		
11:50	A-3 H. Tsuda (Kyoto Univ.)		
12:00	Modeling and Simulation of Nanoscale Surface Roughness during Plasma Etching of Si: Mechanism and Reduction		
12:10	A-4 F. Isono (Waseda Univ.)	Lunch	
12:20	In-Situ Scanning Tunneling Microscopy of Shadowing Effects of Angled Ion Implantation on Patterned Si Surface		
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13:30	<Invited> B-1 T. Shimizu (Max-Planck Inst.) Non-Thermal Plasma at Atmosphere for Medicine and Hygiene		
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14:20	<Invited> B-2 H. Sakakita (AIST) Introduction of Low Temperature and Reactive Plasmas to Minimally Invasive Surgery as a Novel Hemostatic Technique		
14:30			
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14:50	B-3 K. Ishikawa (Nagoya Univ.)	Arranged Session Plasma Biological Treatment and Medicine	
15:00	Plasma-Biological Surface Interaction for Food Hygiene: Real-time in situ electron spin resonance		
15:10	Break		
15:20	Break		
15:30	C-1 T. Okumura (Panasonic)	Atmospheric Pressure Plasma and non-plasma Reaction	
15:40	Elongated Inductively Coupled Thermal Plasma Torch Operable in Atmospheric Pressure		
15:50	C-2 S. Hayashi (Hiroshima Univ.)		
16:00	A Physical Model for Leading Wave Crystallization Induced by Micro-Thermal-Plasma-Jet Irradiation to Amorphous Silicon Films		
16:10	C-3 S. Tajima (Nagoya Univ.)	Break	
16:20	Evaluation of gas-surface reaction dynamics during the plasmaless Si etching using NO/F2 gas mixture		
16:30	Break		
16:40	<Invited> D-1 T. Hirai (SONY) Quality control for dry process through APC/EES		
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17:30	<Invited> D-2 D. Djurdjanovic (Univ. of Texas) Modeling and Prediction of Degradation in Complex Systems Operating Under Variable Operating Condition		
17:40			
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18:00			
18:10	D-3 M. Ito (Lam Research)	Manufacturing Technology	
18:20	TEOS Etch Rate Predictions Using Virtual Metrology		
18:30	D-4 H. K. Lee (Samsung)		
18:40	Innovative APC, Using Virtual Metrology with Advanced Sensors		
18:50	Banquet		
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November 16

8:00	Registration		
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9:00	<Invited> E-1 T. Kato(Tohoku Univ.) Controllable graphene growth using novel plasma catalytic deposition		Novel Plasma Deposition and monitoring
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9:50	E-2 Y. Abe (Nagoya Univ.) High performances of microcrystalline Si thin film formation for a solar cell by measurement and control of hydrogen radicals in the SiH4/H2 plasma		
10:00	E-3 Y. Setsuhara (Osaka Univ.) Development of ICP-Enhanced Reactive Sputtering System with Multiple Low- Inductance Antenna Modules for Large-Area Deposition of Silicon Films		
10:10	E-4 A. Pandey (Chubu Univ.) Monitoring of electron density and wall deposit by curling probe during plasma process		
10:20			
10:30	Break		
10:40	Poster session		
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11:30	Core A		Core B
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12:30	Lunch		
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13:10	Arranged Session Non-Volatile Memory Processes		
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13:50	<Invited> F-1 N. Takaura (LEAP) Recent Progress in Non-Volatile Devices and Processes for Low-Power Electronics		
14:00			
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14:20	<Invited> F-2 K. Suu (Ulvac) The development of etching technology for non-volatile memories		
14:30			
14:40			
14:50	F-3 A. Yamaguchi (Hyogo Univ.) GCIB etching under acetic acid vapor for etch-resistant materials		
15:00	F-4 K. Karahashi (Osaka Univ.) Etching reactions of CoFeB By Ar+ and CO+ ion irradiation		
15:10			
15:20	Break		
15:30	Break		
15:40	Etching Technology		
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16:20	G-2 M. Kamibayashi (Hitachi) Effect of Wafer-bias Frequency on Selectivity and Gate-etch Profile in the Gate-last Fin-FET Process		
16:30	G-3 K. Miyake (Osaka Univ.) Evaluation of sputtering yields of silicon nitride by fluorohydrofluorocarbon ions by molecular dynamics (MD) simulations: modeling of thermal relaxation processes for polymer formation		
16:40			
16:50	H-1 M. Fukasawa (Sony) Photon-stimulated surface reaction and generation of damage to hydrogenated silicon nitride in fluorocarbon plasma		Plasma Damage
17:00	H-2 A. Matsuda (Kyoto Univ.) Three-Dimensional Parameter Mapping of Annealing Processes for HBr/O2-Plasma-Induced Damages in Si Substrates		
17:10	H-3 Z. Liu (Nagoya Univ.) An in-situ sequential H and N radical exposure process for recovery of plasma-damaged GaN		
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17:40	Closing Remark (Negishi)		
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